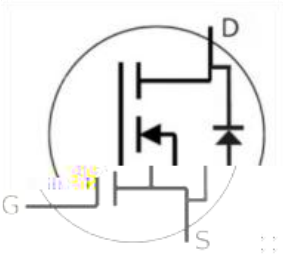
S1M075120B2

TriQSiC™1200V Silicon Carbide Power MOSFET G1

Features

-
-
-
-
-
-
-
-
-



Benefits

-
-
-
-
-

Part number	Die size W x L mm

Applications

-
-
-
-

Table 1 Key performance and package parameters

Type	V_{DS}	I_{DS} ≤	$R_{DS(on),\ typ}$	$T_{J,max}$

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3 Electrical characteristist ..... **har** ..... **r**

1 Maximum ratings

Table 2 Maximum rating

Symbol	Parameter	Value	Unit	Test Conditions	Note
				≤	

2 Electrical characteristics

2.1 Static characteristics

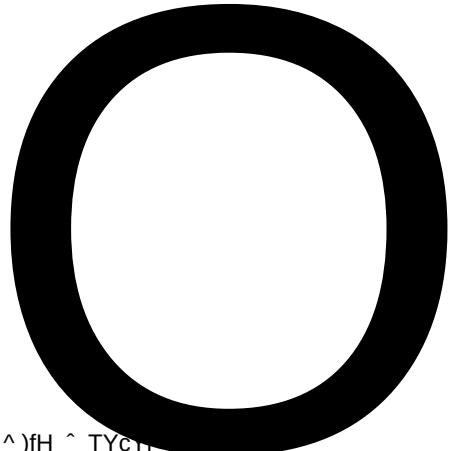
Table 3 Static characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note

2.3 Switching characteristics

Table 5 Dynamic characteristics (

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note

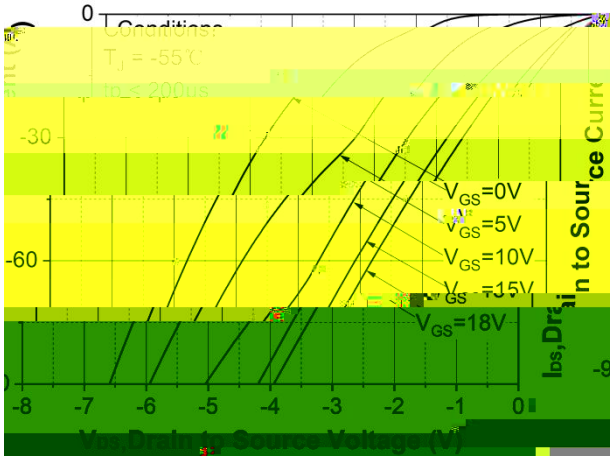


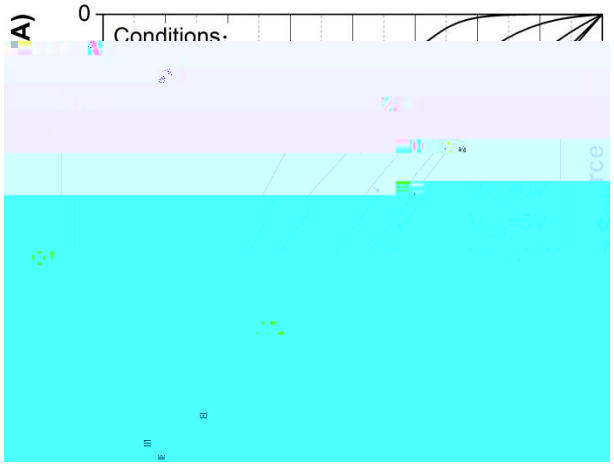
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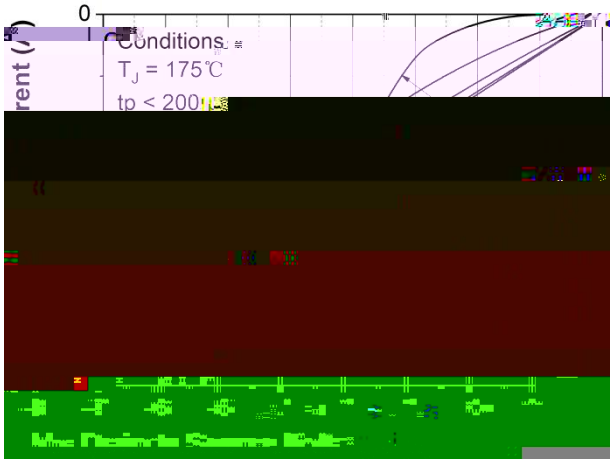
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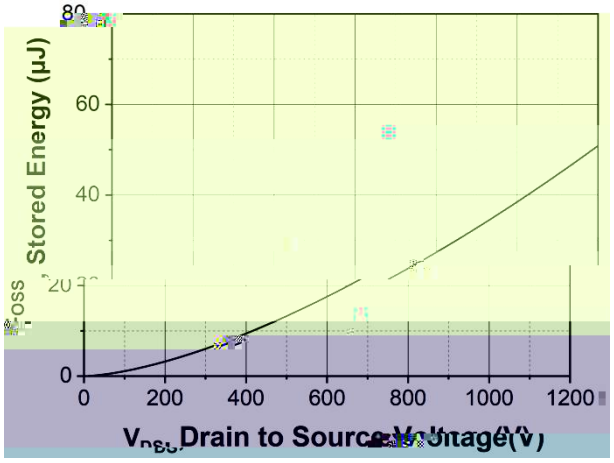
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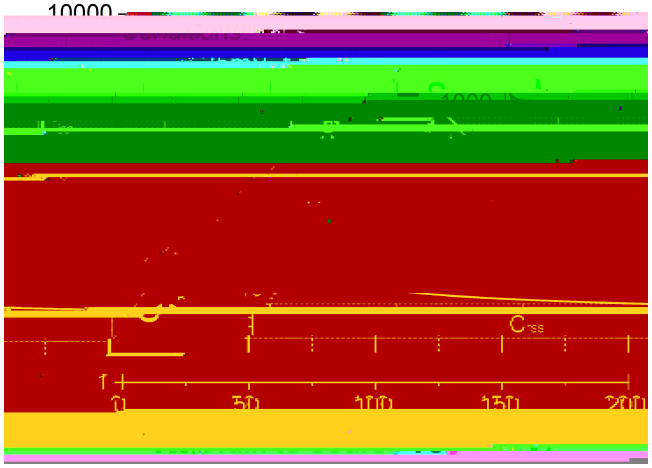
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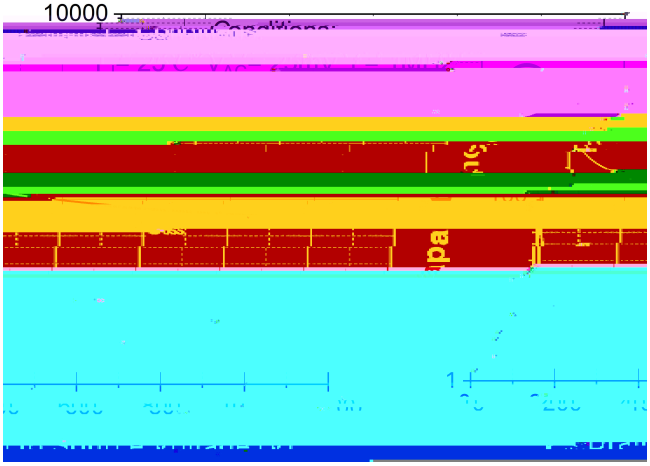










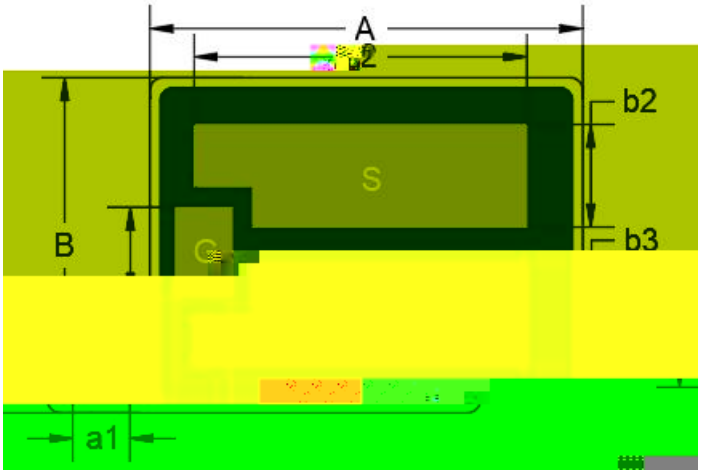


4 Mechanical parameters

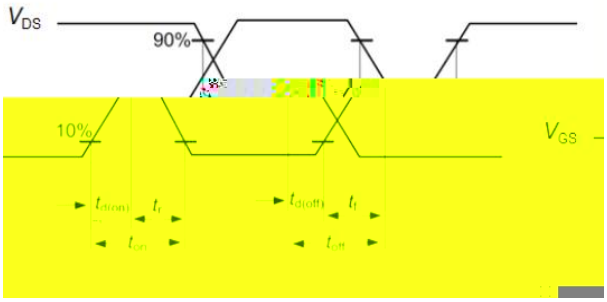
4.1 Dimensions and metallization

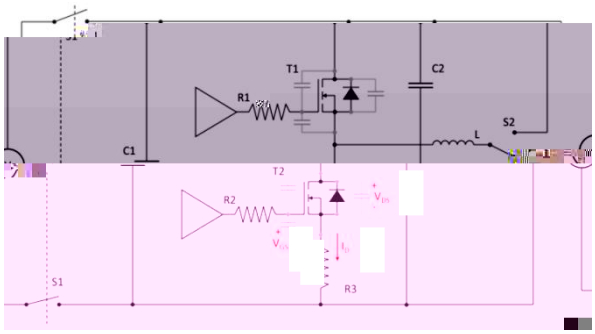
Parameter	Typical value	Unit	Metallization

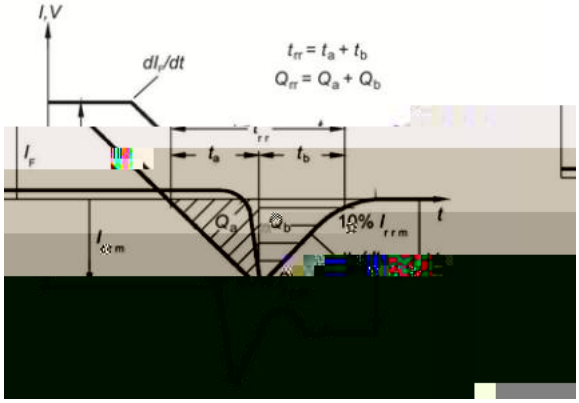
4.2 Layout



5 Test conditions







S1M075120B2

1200V SiC Power MOSFET

Revision history

Document version	Date of release	Document stage	Description of changes
V01_00	2022-09-26	——	——
V01_01	2023-04-05	——	——
V01_01	2023-09-15	——	——
V01_03	2024-09-24	——	——
V02_00	2025-03-31	——	——
V03_00	2025-04-09	——	——
V03_01	2025-12-22	Final	——

Attention

RoHS compliance

REACH compliance

S1M